



FZT1149A

### 25V PNP MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

### **Features and Benefits**

- BV<sub>CEO</sub> > -25V
- Maximum Continuous Current I<sub>C</sub> = -4A
- Peak Pulse Current I<sub>C</sub> = -10A
- High Gain Holds Up h<sub>FE</sub> > 195 @I<sub>C</sub> = -2A
- Very Low Equivalent On-Resistance; R<sub>CE(sat)</sub> = 130mΩ at -2A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

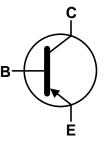
### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.112 grams (Approximate)

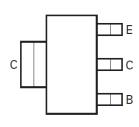
SOT223



Top View



Device Symbol



Top View Pin Out

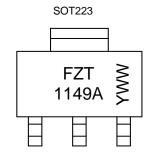
## **Ordering Information** (Note 4)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT1149ATA	AEC-Q101	FZT1149A	7	12	1.000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



FZT 1149A = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W$  = Week Code (01~53)



# Absolute Maximum Ratings (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-30	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-25	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	Ic	-4	Α
Base Current	I <sub>B</sub>	-500	mA
Peak Pulse Current	I <sub>CM</sub>	-10	Α

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Dower Dissipation	(Note 6)	Б	2.0	W	
Power Dissipation	(Note 7)	P <sub>D</sub>	1.6		
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Peniatones, Junation to Ambient	(Note 6)	D	62.5	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	78.1		
	(Note 8)		104	1	
Thermal Resistance Junction to Lead (Note 9)		$R_{ hetaJL}$	10.9		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

### ESD Ratings (Note 10)

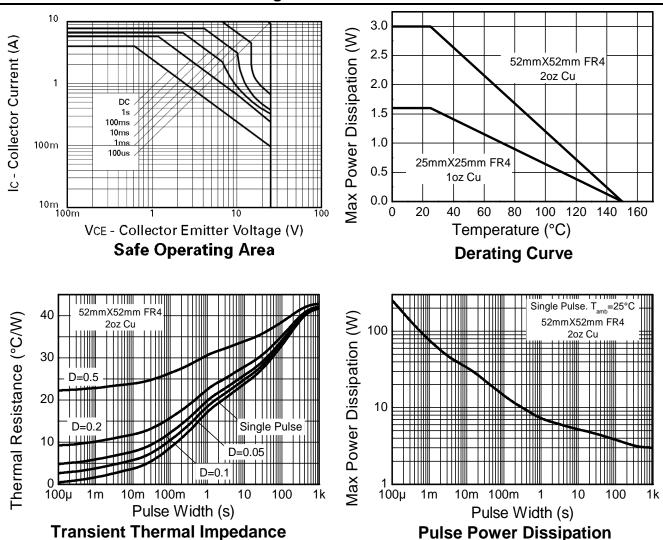
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as note (5), except the device is mounted on minimum recommended pad layout.
- Thermal resistance from junction to solder-point (at the end of the collector lead).
  Refer to JEDEC specification JESD22-A114 and JESD22-A115.



# **Thermal Characteristics and Derating Information**





# Electrical Characteristics (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-30	-70	-	V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	-25	-60	-	V	$I_C = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	$BV_CEO$	-25	-60	-	V	$I_C = -10mA$
Collector-Emitter Breakdown Voltage	$BV_CEV$	-25	-60	-	V	$I_C = -100 \mu A$ , $V_{EB} = -1 V$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-7	-8.5	-	V	$I_E = -100 \mu A$
Collector Cut-Off Current	I <sub>CBO</sub>	-	-0.3	-20	nA	V <sub>CB</sub> = -24V
Collector Cut-Off Current	I <sub>CES</sub>	-	-0.3	-20	nA	V <sub>CES</sub> = -24V
Emitter Cut-Off Current	I <sub>EBO</sub>	-	-0.3	-20	nA	$V_{EB} = -6V$
		270	450	-	-	$I_C = -10mA$ , $V_{CE} = -2V$
		250	400	800		$I_C = -0.5A$ , $V_{CE} = -2V$
DC Current Transfer Static Ratio (Note 11)	h <sub>FE</sub>	195	320	-		$I_C = -2A$ , $V_{CE} = -2V$
		115	190	-		$I_C = -5A$ , $V_{CE} = -2V$
			50	-		$I_C = -10A$ , $V_{CE} = -2V$
	VCE(sat)	-	-45	-80	mV	$I_C = -0.1A$ , $I_B = -1mA$
		-	-100	-170		$I_C = -0.5A$ , $I_B = -3mA$
Collector-Emitter Saturation Voltage (Note 11)		-	-140	-240		$I_C = -1A$ , $I_B = -7mA$
		-	-170	-260		$I_C = -2A$ , $I_B = -30mA$
		-	-230	-350		$I_C = -4A, I_B = -140mA$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	-	-960	-1,050	mV	$I_C = -4A$ , $I_B = -140mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	-	-860	-1,000	mV	$I_C = -4A, V_{CE} = -2V$
Transitional Frequency	$f_{T}$	-	135	-	MHz	$I_C = -50$ mA, $V_{CE} = -10$ V, $f = 50$ MHz
Output Capacitance	C <sub>obo</sub>	-	50	-	pF	$V_{CB} = -10V$ , $f = 1MHz$ ,
Switching Time	t <sub>on</sub>	-	150	-	ns	$V_{CC} = -10V, I_{C} = -4A,$
Switching Tille	t <sub>off</sub>	-	270	-	ns	$I_{B1} = I_{B2} = \pm 40 \text{mA}$

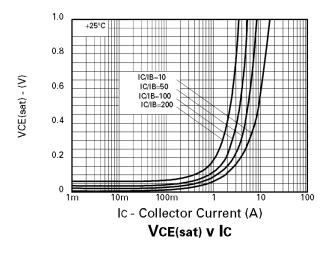
Note: 11. Measured under pulsed conditions. Pulse width =  $300\mu s$ . Duty cycle  $\leq 2\%$ .

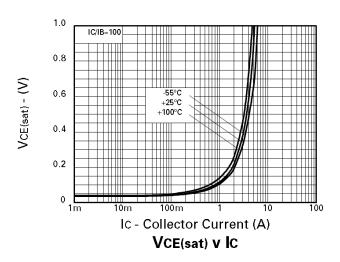
January 2016

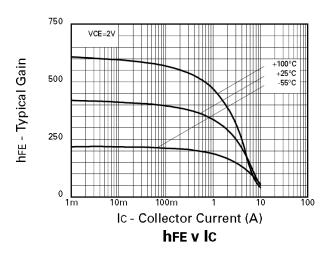
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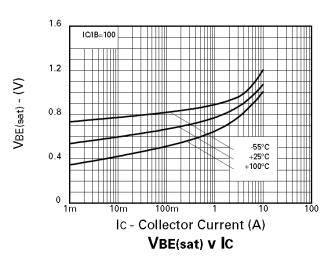


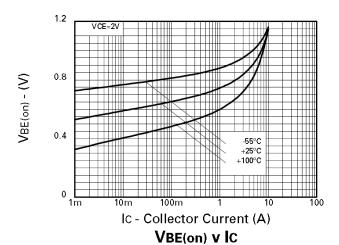
## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







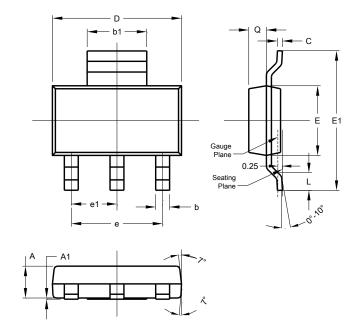






## **Package Outline Dimensions**

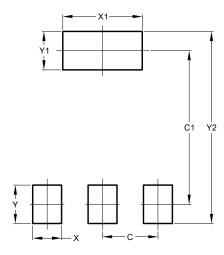
Please see AP02001 at http://www.diodes.com/\_files/datasheets/ap02001.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/\_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)	
С	2.30	
C1	6.40	
Х	1.20	
X1	3.30	
Y	1.60	
Y1	1.60	
Y2	8.00	



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